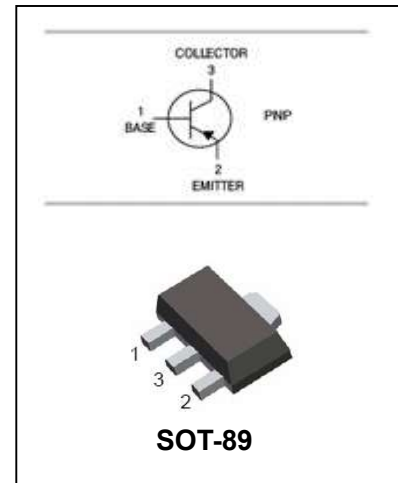


Silicon Planar Epitaxial Transistor

2SA1662

FEATURES

- Complementary to KTC4374



ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1662	FO/FY	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.4	A
P_C	Collector Power Dissipation	500	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

Silicon Planar Epitaxial Transistor

2SA1662

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-80			V
Collector- emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-80			V
Emitter- base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-80V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-50mA$	70		240	
		$V_{CE}=-2V, I_C=-200mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-200mA, I_B=-20mA$			-0.4	V
Base-emitter	V_{BE}	$V_{CE}=-2V, I_C=-5mA$	-0.55		-0.8	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		14		pF

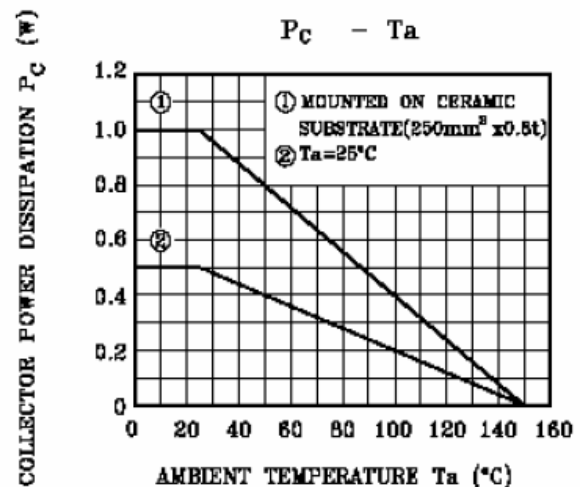
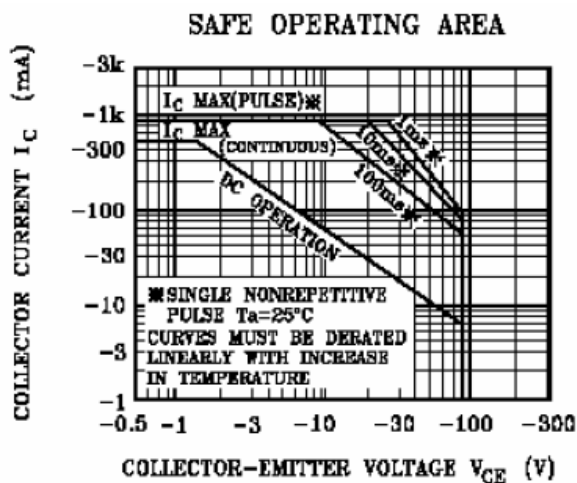
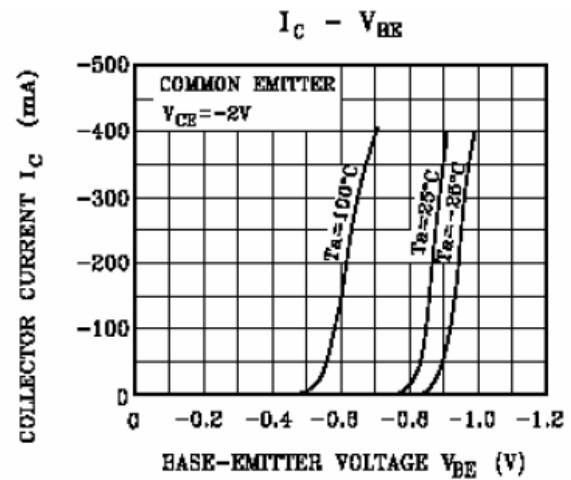
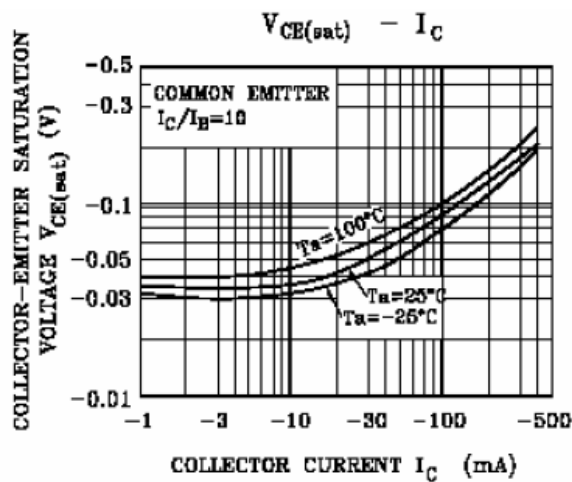
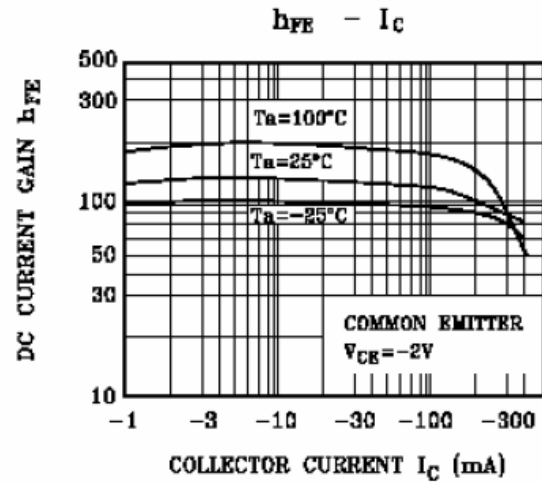
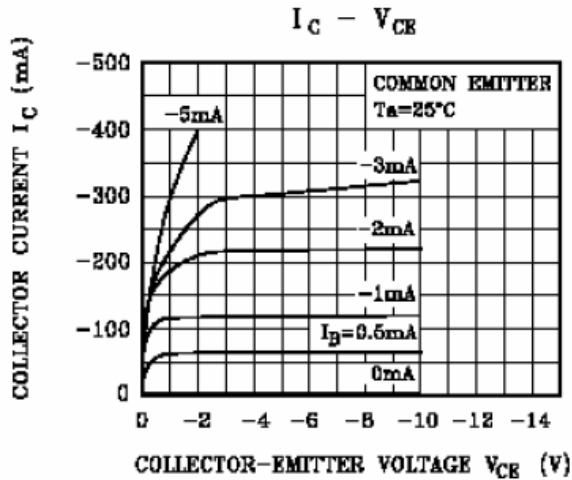
CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240
Marking	FO	FY

Silicon Planar Epitaxial Transistor

2SA1662

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



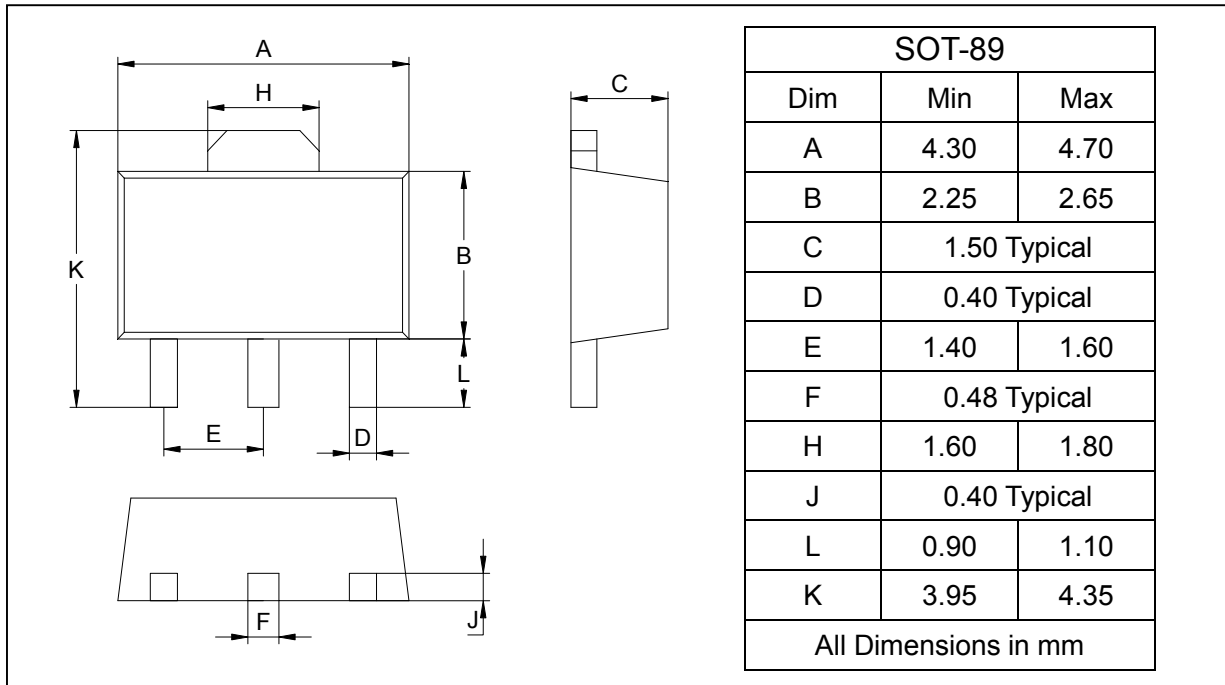
Silicon Planar Epitaxial Transistor

2SA1662

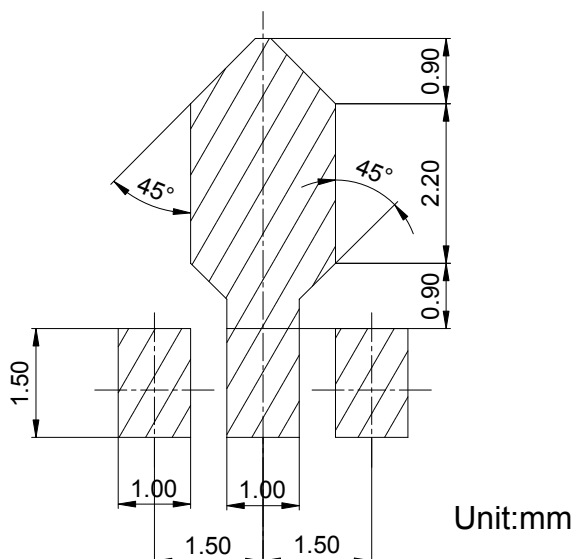
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1662	SOT-89	1000/Tape&Reel